



## ***MH490 Specifications***

### **High Speed High Accuracy Programmable Linear Hall Sensor**

MH490 is a monolithic programmable Hall sensor IC featuring the planar Hall technology, which is sensitive to the flux density applied orthogonally to the IC surface. The sensor provides an output signal proportional to the applied magnetic flux density and is preferably suited for current measurement.

The transfer characteristic of MH490 is factory trimmed over temperature, and is programmable (offset, gain) during end-of-line customer calibration. The linear analog output is designed for applications where a very fast response is required, such as inverter applications.

In a typical application, the sensor is used in combination with a soft ferromagnetic core. This core is recommended to be laminated for high bandwidth applications. The Hall IC is placed in a small air gap and the current conductor is passed through the inner part of the ferromagnetic core.

The core concentrates and amplifies the magnetic flux on the Hall sensor IC, which generates an output voltage proportional to the current flowing in the conductor.

Broken ground wire detection, clamps, power-on reset, and under/overvoltage detection provide the required diagnostics for safety-critical automotive applications.

#### ***Features and Benefits***

- End-of-line programmable sensor
- User-selectable internal or external reference voltage
- User-selectable ratiometry of QVO
- User-selectable ratiometry of Sensitivity
- Measurement range from  $\pm 0.9$  to  $\pm 25$  mV/G
- Wideband sensing: DC to 240 KHz
- Very short response time  $\sim 2 \mu\text{s}$
- RoHS compliant
- TO94(4-pin) package
- MSL-1
- Automotive Grade AECQ100 with diagnostics for safety-critical

#### ***Applications***

- High Voltage Traction Motor Inverter
- 48V Boost Recuperation Inverter
- DC/DC Converter
- BLDC motor current monitoring
- Smart Fuse Overcurrent Detection



**Company Name and Product Category**

MH:MST Hall Effect/MP:MST Power IC

**Part number**

181,182,183,184,185,248,249,276,477,381,381F,381R,382.....

If part # is just 3 digits, the forth digit will be omitted.

**Temperature range**

E: 85 °C, I: 105 °C, K: 125 °C, L: 150 °C

**Package type**

UA:TO-92S, VK:TO-94(4pin), VF:TO-92S(5pin),  
 SO:SOT-23,SQ:QFN-3,ST:TSOT-23,SN:SOT-553,  
 SF:SOT-89(5pin),SS:TSOT-26,SD:DFN-6

**Sorting**

$\alpha$ ,  $\beta$ , Blank.....

Part No.	Temperature Suffix	Package Type
MH490KVK	K (-40°C to + 125°C)	VK (To-94-4pin)
MH490MKVK	K (-40°C to + 125°C)	VK (To-94-4pin)

The block diagram illustrates the internal architecture of the ADXL045 digital accelerometer. The system is contained within a yellow rounded rectangle. Key components include:

- HALL PLATES:** Four square plates arranged in a 2x2 grid, connected to a **BIAS** input.
- regulator:** Receives **VCC** and provides **VDD** to the internal circuitry.
- oscillator:** Provides a clock signal to the **EEPROM and Control Logic**.
- Temp. Sensor:** Provides temperature data to the **EEPROM and Control Logic**.
- EEPROM and Control Logic:** The central processing unit, receiving inputs from the oscillator and temperature sensor, and controlling the **offset control** and **Sensitivity control** blocks.
- offset control:** Receives signals from the **EEPROM and Control Logic** and the first stage of the signal path.
- Sensitivity control:** Receives signals from the **EEPROM and Control Logic** and the second stage of the signal path.
- Signal Path:** A series of four operational amplifiers (represented by triangles) that process the signal from the hall plates through the control blocks to produce the **VOUT** signal.
- VDD, GND, VOUT, NC:** External pins for power, ground, output, and no connection, respectively.

## MH490 Specifications

### High Speed High Accuracy Programmable Linear Hall Sensor

#### Absolute Maximum Ratings At ( $T_A = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Positive Supply Voltage (overvoltage)	$V_{DD}$	10.5	V
Reverse Voltage	$V_{SREV}$	-0.3	V
Positive Output Voltage	$V_{OUT}$	5.5	V
Output Sink Current	$I_{Sink}$	-40	mA
Output Source Current	$I_{Source}$	60	mA
Reverse Output Voltage	$V_{OREV}$	-0.3	V
Reverse Output Current	$I_{OREV}$	-50	mA
Operating Ambient Temperature Range	$T_A$	-40 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_S$	-40 to +150	$^\circ\text{C}$
ESD – Human Body Model	$ESD_{HBM}$	8	KV
Maximum Number of EEPROM Write Cycles	$EEPROM_{W(max)}$	1000	cycle

**Note:** Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum - rated conditions for extended periods of time may affect device reliability.

#### General Electrical Specifications

Operating Parameters  $T_A = -40$  to  $125^\circ\text{C}$ ,  $V_{DD} = 5V \pm 10\%$ , unless otherwise specified.

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Nominal Supply Voltage	$V_{DD}$		4.5	5	5.5	V
Supply Current	$I_{DD}$	No OUT load		13	18	mA
Power-On Reset Voltage	$V_{POR(H)}$	$T_A = 25^\circ\text{C}$ , $V_{DD}$ rising	2.82	3.0	3.25	V
	$V_{POR(L)}$	$T_A = 25^\circ\text{C}$ , $V_{DD}$ falling	2.58	2.8	3.06	V
Power-On Reset Hysteresis	$V_{POR(HYS)}$	$T_A = 25^\circ\text{C}$	158	200	190	mV
Power-On Delay Time	$t_{PO}$	$T_A = 25^\circ\text{C}$ , $C_{BYPASS} = 104$ , $CL = 1$ nF			1	ms
Overvoltage Detection	$V_{OVD(EN)}$	$T_A = 25^\circ\text{C}$	6.35	6.50	6.70	V
	$V_{OVD(DIS)}$	$T_A = 25^\circ\text{C}$	5.85	6.00	6.20	V
OVD Hysteresis	$V_{OVD(HYS)}$	$T_A = 25^\circ\text{C}$		0.50		mV
Undervoltage Detection	$V_{UVD(H)}$	$T_A = 25^\circ\text{C}$	4.10	4.20	4.35	V
	$V_{UVD(L)}$	$T_A = 25^\circ\text{C}$	3.70	3.80	3.95	V
UVD Hysteresis	$V_{UVD(HYS)}$	$T_A = 25^\circ\text{C}$		400		mV
OVD and UVD Enable/Disable Delay Time	$t_{VD(EN)}$	$T_A = 25^\circ\text{C}$	7	14	21	us
	$t_{VD(DIS)}$	$T_A = 25^\circ\text{C}$	7	14	21	us
Linear Output Range	$V_{OLIN}$	pull-down $\geq 10$ k $\Omega$	10		90	%Vdd

### Analog output specification

Accuracy specifications

Operating Parameters  $T_A = -40$  to  $125^\circ\text{C}$ ,  $V_{DD} = 5V \pm 10\%$ , unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Output Impedance	$R_{OUT}$	Normal Operation		8		$\Omega$
Output Capacitive Load	$C_L$			10	68	nF
Output Resistive Load	$R_L$		4.7	10		K $\Omega$
VOUT pin sink/source current		$V_{OUT}$ shorted to $V_{DD}$			-20	mA
		$V_{OUT}$ shorted to $G_{ND}$	28			mA
Output Voltage Clamp	$V_{CLP(HIGH)}$	$T_A = 25^\circ\text{C}$ , $R_L = 10\text{ K}\Omega$ to GND, Bias = 400 G		$V_{DD} - (V_{DD} * 0.06)$	$V_{DD} - 0.25$	V
	$V_{CLP(LOW)}$	$T_A = 25^\circ\text{C}$ , $R_L = 10\text{ K}\Omega$ to $V_{DD}$ , Bias = 400 G	0.25	$V_{DD} * 0.06$		V
Output Voltage with Broken GND/VDD	$V_{BRK\_DN}$	$T_A = 25^\circ\text{C}$ , $R_L = 10\text{ K}\Omega$ to GND, Pin 3 = NC		100	200	mV
	$V_{BRK\_UP}$	$T_A = 25^\circ\text{C}$ , $R_L = 10\text{ K}\Omega$ to $V_{DD}$ (5V), Pin 3 = NC	4.8	4.9	5	V
$V_{OQ}$ Ratiometry	$\Delta^R V$	$V_{DD} = 5V \pm 5\%$ , $V_{OQ} = 50\% V_{DD}$		$\pm 0.24$	$\pm 0.4$	% $V_{OQ}$
RMS Output Noise(high-gain)	$N_{RMS-HG}$	Values for $S=12.5\text{mV/G}$ , 1KHz-100KHz		7		mVRMS
Temperature coefficient variation of Sensitivity	$\delta_{TCVO}$	Over full range of BM and $T_A$ , calibrated IC, without $TC_{OF}$	-200		200	ppm/ $^\circ\text{C}$
Offset Temperature characteristic	$TC_{VOF}$	BM = 0G, $S=12.5\text{mV/G}$ , $V_{OUT} - V_{DD}/2$	-0.120		0.120	mV/ $^\circ\text{C}$
Average Fine Sensitivity Programming Step Size	$\text{Step}_{SENS}$	$S=12.5\text{mV/G}$ , $T_A = 25^\circ\text{C}$		1.5		$\mu\text{V/G}$

**Note:** The accuracy specifications are defined for the factory calibrated sensitivity. The achievable accuracy is dependent on the user's end-of-line calibration.

### Timing specifications

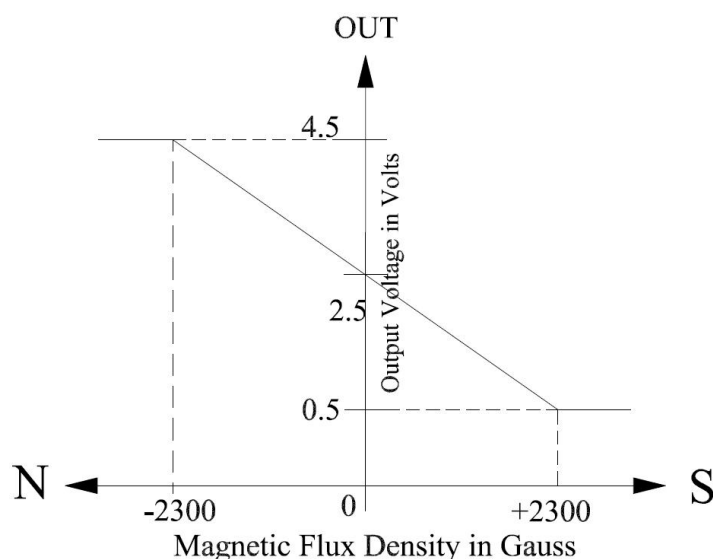
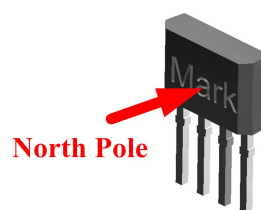
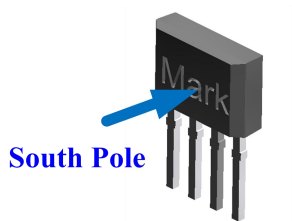
Operating Parameters  $T_A = -40$  to  $125^\circ\text{C}$ ,  $V_{DD} = 5V \pm 10\%$ , unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Response Time	tRESP	$T_A = 25^\circ\text{C}$ , $C_L=1\text{nf}$ , Magnetic field step of 400G, Sens=2mV/G, Measured 90% input to 90% output.		2		$\mu\text{s}$
Frequency bandwidth	BW	-3 dB, $T_A = 25^\circ\text{C}$		240		kHz

### Magnetic specification

Operating Parameters  $T_A = -40$  to  $125^\circ\text{C}$ ,  $V_{DD} = 5V \pm 10\%$ , unless otherwise specified.

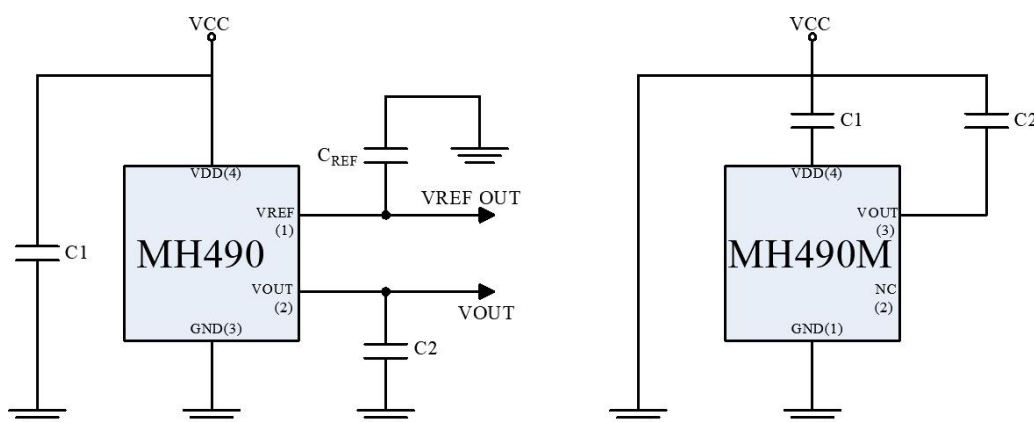
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Operational Magnetic Field Range	BOP		$\pm 100$	$\pm 1000$	$\pm 2300$	G
Programmable Sensitivity	S		0.9	2	25	mV/G
Linearity Error (Magnetic)	NL	$V_{OUT}$ in $[10\%V_{DD}, 90\%V_{DD}]$ , $T_A = 25^\circ\text{C}$ , $R_L \geq 10\text{ k}\Omega$			$\pm 0.25$	%FS



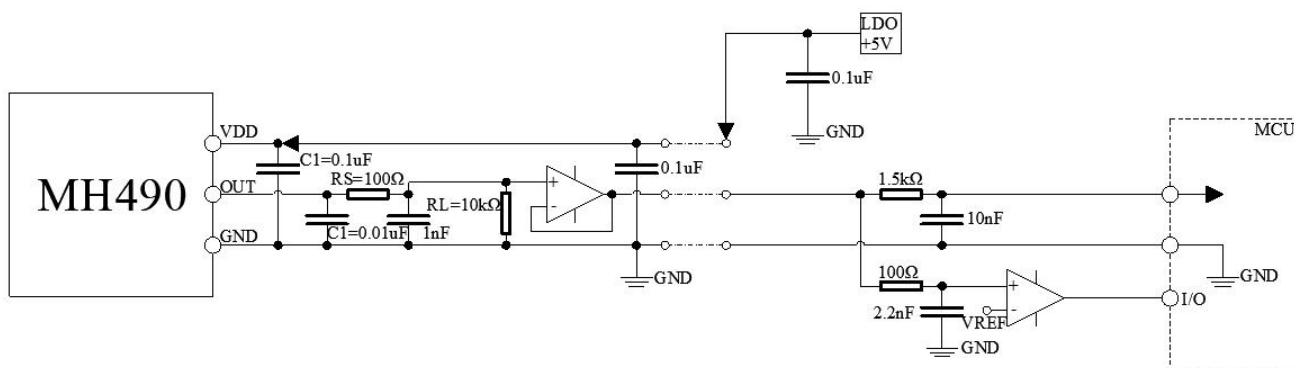
### Programmable Items

Parameter	Bits	Factory Setting	Comment
QVO[4:0]	5	trimmed	Quiescent output level (0 Gauss) adjustment
RG[4:0]	5	trimmed	Rough gain adjustment
FG[7:0]	8	trimmed	Fine gain adjustment
POL	1	0	0: default polarity as described in section 11 (figure 4) 1: opposite polarity
ID[19:0]	20		CUSTOMER ID

### Recommended Application Diagram



### Application Circuit for Harsh and Noisy Environment



For proper operation a 100nF or bigger bypass capacitor C1 should be placed as close as possible to the VDD and GND pins, and a bypass capacitor C2 of 1nF to 10nF can be placed on the output of MH490.

### ESD Precautions

Electronic semiconductor products are sensitive to Electro Static Discharge (ESD). Always observe Electro Static Discharge control procedures whenever handling semiconductor products.

### Under- and overvoltage detection (UVD, OVD)

Under- and overvoltage detection is implemented to prevent the device from operating outside the required supply voltage range. A fault condition is detected if the supply voltage is below or above the limits. The undervoltage detection is kept in reset (undervoltage detected) during the start-up of the device and is released by the digital as soon as the digital finished the EEPROM reading. The overvoltage detection can be enabled/disabled by the EEPROM.

The outputs of the UVD and OVD are used to force the VREF and VOUT to predefined states incase of a detected fault.

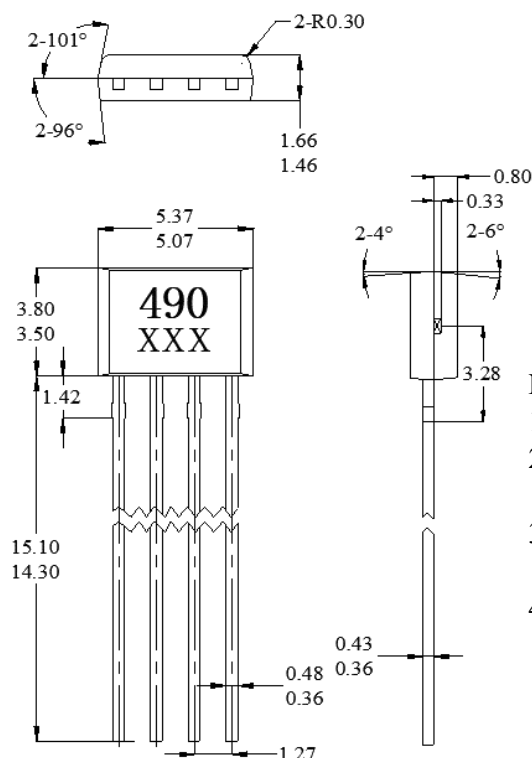
Condition	Description	VREF output	VOUT output
UVD	During device startup and UVD detected	Forced to GND	Floating (Hi-Z)
OVD	OVD detected (only when EN_OVD = 1)	VREF	Floating (Hi-Z)

The VREF output is forced to GND during startup of the device and at an undervoltage condition. The VREF output stays in normal operation at an overvoltage condition.

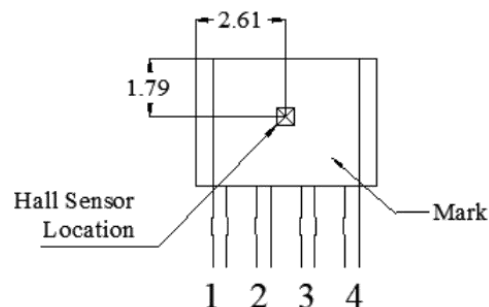
The V<sub>OUT</sub> output is forced to Hi-Z mode in both the UVD and OVD condition. These fault conditions can be detected by a connected controller in case a pull-up or pull-down resistor at V<sub>OUT</sub> is used (V<sub>OUT</sub> = V<sub>CC</sub> or V<sub>OUT</sub> = GND).

### ***MH490 Sensor Location, package dimension and marking***

#### **VK Package (To-94-4pin)**



#### **Hall Chip location**



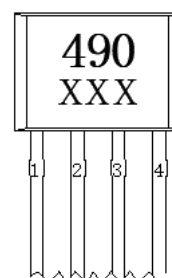
#### **NOTES:**

1. Controlling dimension: mm
2. Leads must be free of flash and plating voids
3. Do not bend leads within 1 mm of lead to package interface.

#### **4. PINOUT:**

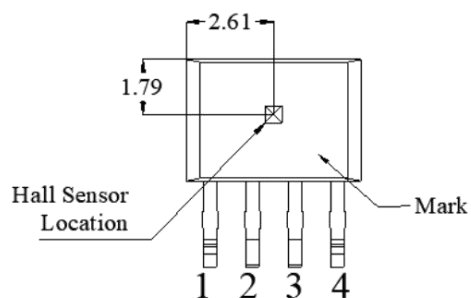
Pin 1	VREF
Pin 2	VOUT
Pin 3	GND
Pin 4	VCC

#### **Output Pin Assignment**





### VK Package (To-94-4pin)



1. Controlling dimension: mm
2. Leads must be free of flash and plating voids
3. Do not bend leads within 1 mm of lead to package interface.

## Output Pin Assignment

